This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

1. (Currently Amended) A photovoltaic element comprising

a photon absorber consisting essentially of silicon;

an electrically conductive large-surface working element, consisting essentially of metal, that is at least partly embedded in the photon absorber, for a higher efficiency of the photovoltaic element,

wherein the working element is a parallelepiped, and

the working element being separated from the photon absorber by a phase boundary, and the working element having a greater electron mobility than the photon absorber;

at least one conductor that is at least partly embedded in the photon absorber;

the volume ratio of the photon absorber to at least one conductor is in the range of between 2 to 7, and

the conductors ~~at least one conductor~~ has essentially the same composition as the working element.

2. (Previously Presented) The photovoltaic element of claim 1, characterized in that the working element is substantially electrically insulated from a positive and a negative pole of the photovoltaic element.

3. (Cancelled)

4. (Previously Presented) The photovoltaic element of claim 1, characterized in that the working element and the at least one conductor is elongate and substantially parallel to each other.

5. (Previously Presented) The photovoltaic element of claim 1, characterized in that the at least one conductor is a plurality of conductors wherein at least one of said plurality of conductors is configured as a positive conductor and at least one of said plurality of conductors is configured as a negative conductor, the positive conductor ending at or protruding beyond a first front side of the photon absorber and the negative conductor ending at or protruding beyond a second front side of the photon absorber.

6. (Previously Presented) The photovoltaic element of claim 5, characterized in that at least two photon absorbers are provided in a multi-layered structure that are in contact via an abutment surface in which the at least one positive conductor and the at least one negative conductor in each photon absorber are arranged such that the positive conductors and the negative conductors are separated from each other by the abutment surface.

7. (Previously Presented) The photovoltaic element of claim 5, characterized in that a plurality of positive conductors are connected with each other through a first omnibus conductor and a plurality of negative conductors are connected with each other via a second omnibus conductor.

8. (Cancelled)

9. (Previously Presented) The photovoltaic element of claim 6, characterized in that two respective photon absorbers have a mutually anti-parallel crystal structure.

10. (Canceled).

11. (Cancelled)

12. (Previously Presented) The photovoltaic element of claim 1, characterized in that the working element has an electric conductivity higher than 1.4 Ω^{-1} cm^{-1}.

13. (Previously Presented) A photovoltaic device comprising a receiving element with recesses in which at least one photovoltaic element of claim 1 is arranged, wherein

conductors present in the photovoltaic element are each connected to omnibus conductors.

14. (Previously Presented) The photovoltaic device of claim 13, characterized in that a plurality of photovoltaic elements are arranged in the recesses, the recesses being in contact with at least one photon absorber of the photovoltaic element.

15. (Previously Presented) The photovoltaic device of claim 13, characterized in that a plurality of first connecting conductors and a plurality of second connecting conductors are each connected with first current conductors and second current conductors, respectively.

16. (Previously Presented) The photovoltaic device of claim 13, characterized by connecting means for mechanically and electrically connecting at least two photovoltaic devices arranged side by side.

17. (Currently Amended) The photovoltaic element of claim 1 [[8]], characterized in that the photon absorber is substantially made of anisotropic monocrystalline silicon.